# MOSFET – Power, Single, P-Channel, ESD, μCool, UDFN, 2.0x2.0x0.55 mm -20 V, -9.4 A

### **Features**

- UDFN Package with Exposed Drain Pads for Excellent Thermal Conduction
- Low Profile UDFN 2.0x2.0x0.55 mm for Board Space Saving
- Lowest RDS(on) in 2.0x2.0 Package
- ESD Protected
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### **Applications**

- High Side Load Switch
- PA Switch and Battery Switch
- Optimized for Power Management Applications for Portable Products, such as Cell Phones, PMP, DSC, GPS, and others

### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise stated)

Parameter			Symbol	Value	Units
Drain-to-Source Voltage			$V_{DSS}$	-20	V
Gate-to-Source Vol	tage		$V_{GS}$	±8.0	V
Continuous Drain	Steady	T <sub>A</sub> = 25°C	I <sub>D</sub>	-6.4	Α
Current (Note 1)	State	T <sub>A</sub> = 85°C		-4.6	
	t ≤ 5 s	T <sub>A</sub> = 25°C		-9.4	
Power Dissipa- tion (Note 1)	Steady State	T <sub>A</sub> = 25°C	P <sub>D</sub>	1.7	W
	t ≤ 5 s	T <sub>A</sub> = 25°C		3.8	
Continuous Drain	Steady	T <sub>A</sub> = 25°C	I <sub>D</sub>	-4.0	Α
Current (Note 2)	State	T <sub>A</sub> = 85°C		-2.9	
Power Dissipation (	Note 2)	T <sub>A</sub> = 25°C	$P_{D}$	0.7	W
Pulsed Drain Curre	nt	tp = 10 μs	I <sub>DM</sub>	-30	Α
Operating Junction and Storage Temperature		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C	
Source Current (Body Diode) (Note 2)		I <sub>S</sub>	-1.0	Α	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		TL	260	°C	
ESD Rating (HBM) per JESD22-A114F		ESD	>2000	٧	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

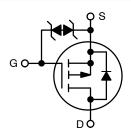
 Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).



# ON Semiconductor®

http://onsemi.com

MOSFET				
$V_{(BR)DSS}$	I <sub>D</sub> MAX			
	29 mΩ @ -4.5 V			
–20 V	39 mΩ @ –2.5 V	-9.4 A		
20 1	60 mΩ @ –1.8 V	0.471		
	120 mQ @ 15 V			



P-Channel MOSFET

### MARKING DIAGRAM



UDFN6 CASE 517BG μCOOL™



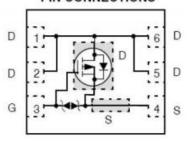
AA = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

### PIN CONNECTIONS



(Top View)

### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

2. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm<sup>2</sup>, 2 oz. Cu.

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Units
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	72	°C/W
Junction-to-Ambient – t ≤ 5 s (Note 3)	$R_{\theta JA}$	33	
Junction-to-Ambient – Steady State min Pad (Note 4)	$R_{\theta JA}$	189	

# **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Co	ondition	Min	Тур	Max	Units
OFF CHARACTERISTICS		•		•	<u>.                                    </u>		-
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I <sub>D</sub> = -250 μA	A, ref to 25°C		-5.0		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = -20 \text{ V}$	$T_{J} = 25^{\circ}C$ $T_{J} = 85^{\circ}C$			-1.0 -10	μΑ
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, \	/ <sub>GS</sub> = ±8.0 V	1		±10	μΑ
ON CHARACTERISTICS (Note 5)		•		•			•
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}$ ,	I <sub>D</sub> = -250 μA	-0.4		-1.0	V
Negative Threshold Temp. Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>				3.0		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = −4.5 \	V, I <sub>D</sub> = -6.4 A		23	29	mΩ
		$V_{GS} = -2.5 \text{ V}, I_D = -4.8 \text{ A}$ $V_{GS} = -1.8 \text{ V}, I_D = -2.5 \text{ A}$			31	39	
					43	60	
		V <sub>GS</sub> = −1.5 \	V, I <sub>D</sub> = -1.5 A		60	120	
Forward Transconductance	9FS	$V_{DS} = -15 \text{ V}, I_D = -4.0 \text{ A}$			18		S
CHARGES, CAPACITANCES & GATE	RESISTANCE						
Input Capacitance	C <sub>ISS</sub>				2600		pF
Output Capacitance	C <sub>OSS</sub>	V <sub>GS</sub> = 0 V <sub>E</sub>	, f = 1 MHz, : −15 V		200		
Reverse Transfer Capacitance	C <sub>RSS</sub>				190		
Total Gate Charge	Q <sub>G(TOT)</sub>				29		nC
Threshold Gate Charge	Q <sub>G(TH)</sub>	V <sub>GS</sub> = −4.5 V,	$V_{DS} = -15 \text{ V};$		1.4		
Gate-to-Source Charge	$Q_{GS}$	I <sub>D</sub> = -	$I_D = -4.0 \text{ A}$		3.7		
Gate-to-Drain Charge	$Q_{GD}$				8.1		
SWITCHING CHARACTERISTICS, VG	S = <b>4.5 V</b> (Note 6)						
Turn-On Delay Time	t <sub>d(ON)</sub>				9.0		ns
Rise Time	t <sub>r</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -4.0 A	$V_{DD} = -15 \text{ V},$		18		
Turn-Off Delay Time	t <sub>d(OFF)</sub>	$I_D = -4.0 A$	$A, R_G = 1 \Omega$		126		
Fall Time	t <sub>f</sub>				71		

# **DRAIN-SOURCE DIODE CHARACTERISTICS**

Forward Diode Voltage	VSD	V <sub>GS</sub> = 0 V,	$T_J = 25^{\circ}C$	0.65	1.0	V
		$I_S = -1.0 A$	T <sub>.1</sub> = 125°C	0.55		

- 3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces). 4. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm<sup>2</sup>, 2 oz. Cu. 5. Pulse Test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%. 6. Switching characteristics are independent of operating junction temperatures.

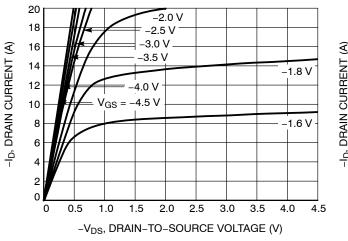
# **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Тур	Max	Units
DRAIN-SOURCE DIODE CHARACTER	RISTICS					
Reverse Recovery Time	t <sub>RR</sub>			25		ns
Charge Time	ta	V <sub>GS</sub> = 0 V, dis/dt = 100 A/μs,		10		
Discharge Time	t <sub>b</sub>	$V_{GS} = 0 \text{ V, dis/dt} = 100 \text{ A/}\mu\text{s,}$ $I_{S} = -1.0 \text{ A}$		15		
Reverse Recovery Charge	Q <sub>RR</sub>			13.6		nC

- 3. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces). 4. Surface-mounted on FR4 board using the minimum recommended pad size of 30 mm<sup>2</sup>, 2 oz. Cu. 5. Pulse Test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%. 6. Switching characteristics are independent of operating junction temperatures.

### TYPICAL CHARACTERISTICS

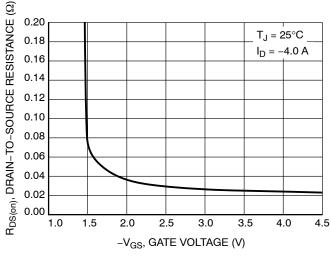
20



 $V_{DS} \le -10 \text{ V}$ 18 -ID, DRAIN CURRENT (A) 16 14 12 10 T<sub>J</sub> = 25°C 6 T<sub>J</sub> = 125°C 2 = -55°C 0 0.5 0 1.0 1.5 2.0 3.0 -V<sub>GS</sub>, GATE-TO-SOURCE VOLTAGE (V)

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



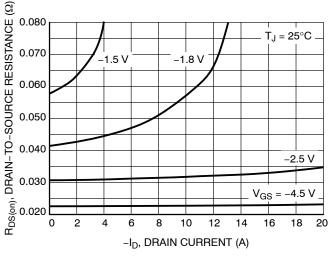
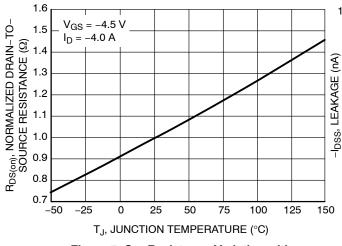


Figure 3. On-Resistance vs. Gate-to-Source Voltage

Figure 4. On-Resistance vs. Drain Current and Gate Voltage



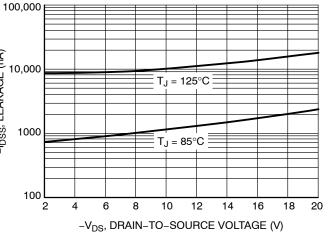


Figure 5. On–Resistance Variation with Temperature

Figure 6. Drain-to-Source Leakage Current vs. Voltage

### **TYPICAL CHARACTERISTICS**

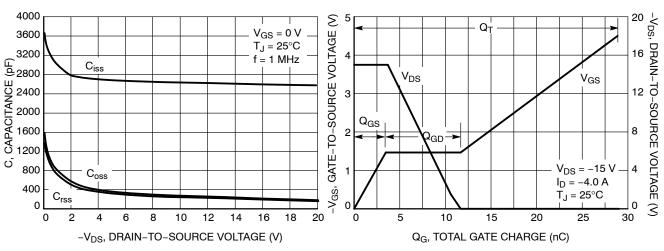


Figure 7. Capacitance Variation

Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

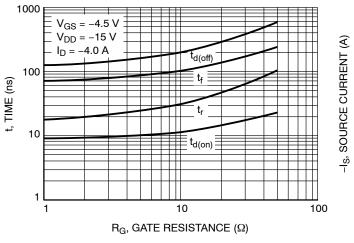


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

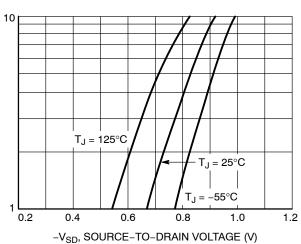


Figure 10. Diode Forward Voltage vs. Current

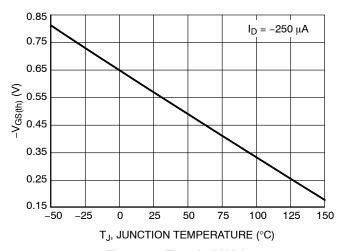


Figure 11. Threshold Voltage

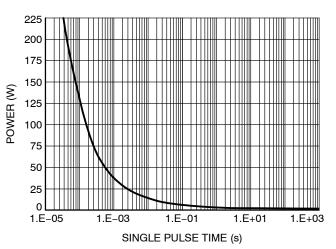
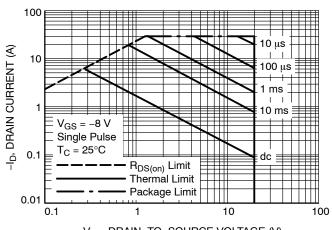


Figure 12. Single Pulse Maximum Power Dissipation

# **TYPICAL CHARACTERISTICS**



 $-V_{DS}$ , DRAIN-TO-SOURCE VOLTAGE (V)

Figure 13. Maximum Rated Forward Biased Safe Operating Area

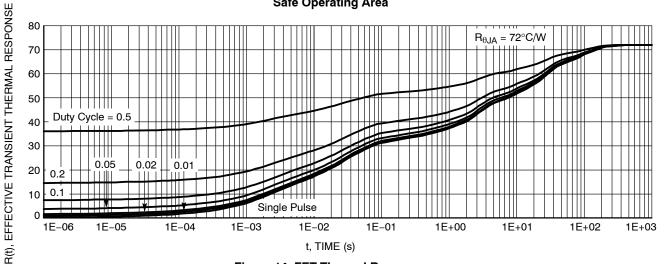


Figure 14. FET Thermal Response

### **DEVICE ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NTLUS3A40PZTAG	UDFN6 (Pb-Free)	3000 / Tape & Reel
NTLUS3A40PZTBG	UDFN6 (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DETAIL A

6X L

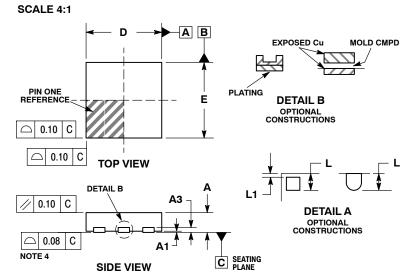
**E2** 

J1

**BOTTOM VIEW** 



**DATE 04 FEB 2010** 



C 0.10

0.05 C NOTE 5

NOTE 3

Ф

0.10 С Α

С 0.05

Α



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION & APPLIES TO PLATED TERMINAL AND IS
  MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL
  COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS
  THE TERMINALS. 3.
- 1. CENTER TERMINAL LEAD IS OPTIONAL CENTER TERMINAL IS CONNECTED TO TERMINAL LEAD # 4.
  2. LEADS 1, 2, 5 AND 6 ARE TIED TO THE FLAG.

	MILLIMETERS					
DIM	MIN	MAX				
Α	0.45	0.55				
A1	0.00 0.05					
A3	0.13	REF				
b	0.25	0.35				
b1	0.51	0.61				
D	2.00	BSC				
D2	1.00 1.20					
E	2.00	BSC				
E2	1.10	1.30				
е	0.65	BSC				
K	0.15	REF				
J	0.27	BSC				
J1	0.65	BSC				
L	0.20 0.30					
L1	0.10					
L2	0.20	0.30				

# **GENERIC MARKING DIAGRAM\***



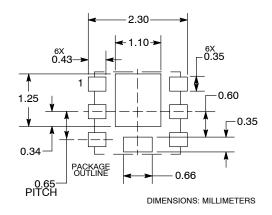
XX = Specific Device Code

M = Date Code

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

### RECOMMENDED **MOUNTING FOOTPRINT**



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DESCRIPTION:	UDFN6 2X2, 0.65P		PAGE 1 OF 1		

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